

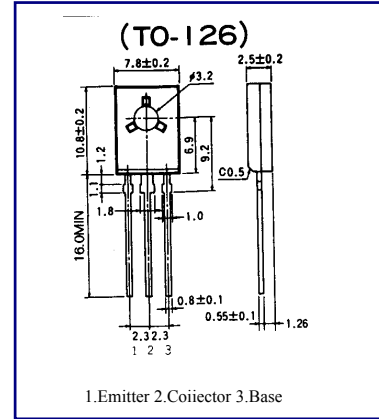


2SB772

# PNP EPITAXIAL SILICON TRANSISTOR

**AUDIO FREQUENCY POWER AMPLIFIER**  
**LOW SPEED SWITCHING**

- Complement to 2SD882



### ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-40	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-30	V
Emitter-Base voltage	V <sub>EB0</sub>	-5	V
Collector Current (DC)	I <sub>c</sub>	-3	A
Collector Current (pulse)	I <sub>c</sub>	-7	A
Base Current (DC)	I <sub>B</sub>	-0.6	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>c</sub>	10	W
Collector Dissipation (T <sub>a</sub> =25°C)	P <sub>c</sub>	1	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C

\*PW ≤ 10ms, Duty Cycle ≤ 50%

### ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = -30V, I <sub>E</sub> = 0			-1	μ A
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = -3V, I <sub>C</sub> = 0			-1	μ A
*DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -20mA	30	150		
	h <sub>FE2</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -1A	60	160	400	
*Collector Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -2A, I <sub>B</sub> = -0.2A		-0.3	-0.5	V
*Base Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -2A, I <sub>B</sub> = -0.2A		-1.0	-2.0	V
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, f = 1MHz, I <sub>E</sub> = 0		45		pF
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>E</sub> = -0.1A		90		MHz

\*Pulse Test: PW ≤ 350μs, Duty Cycles ≤ 2%

### h<sub>FE</sub> (2) CLASSIFICATION

Classification	R	O	Y	G
h <sub>FE</sub> (2)	60-120	100-200	160-320	200-400